

EV318283946



Inventor: **Cem Basc ri**  
Title: **Methods of Forming Capacitor Constructions Comprising Perovskite-Type Dielectric Materials With Different Amount of Crystallinity Regions**

Assignee: **Micron Technology, Inc.**

Serial No.: **09/932,003**

Filed: **August 17, 2001**

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

**PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98**

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, the Examiner's attention is directed to the reference listed on the attached Form PTO-1449 and a copy of which is attached. No admission is made regarding whether the submitted reference is prior art.

Citation of this reference is respectfully requested.

Respectfully submitted,

Date:

9/2/03

Attorney:

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